

Silicon NPN Power Transistors

2SD551

DESCRIPTION

www.datasheet4u.com

- With TO-3 package
- Complement to type 2SB681
- Wide area of safe operation

APPLICATIONS

- For audio frequency power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

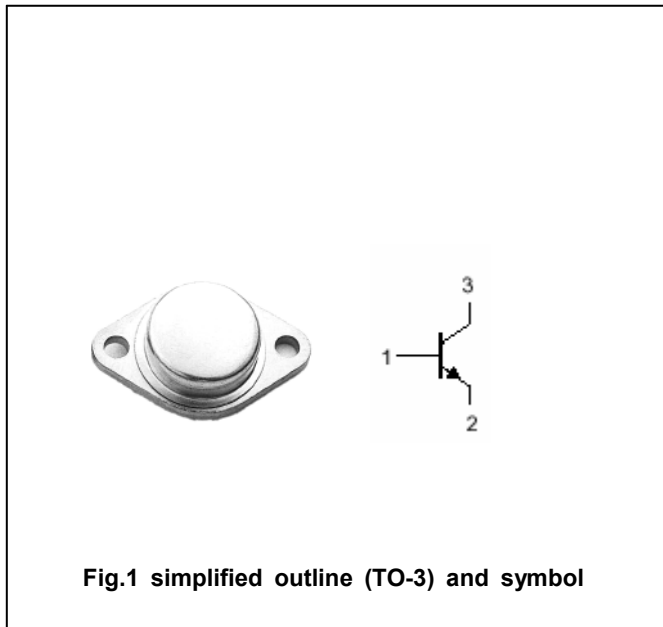


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	150	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		12	A
I _{CM}	Collector current-peak		15	A
P _C	Collector power dissipation	T _C =25□	100	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

Silicon NPN Power Transistors

2SD551

CHARACTERISTICS

T_j=25°C unless otherwise specified

www.datasheet4u.com

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.5	V
V _{BE}	Base-emitter on voltage	I _C =1A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	40		140	
h _{FE-2}	DC current gain	I _C =6A ; V _{CE} =5V	20			
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =10V; f=1MHz		250		pF
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		15		MHz

◆ h_{FE} Classifications

O	R
40-80	70-140

PACKAGE OUTLINE

www.datasheet4u.com

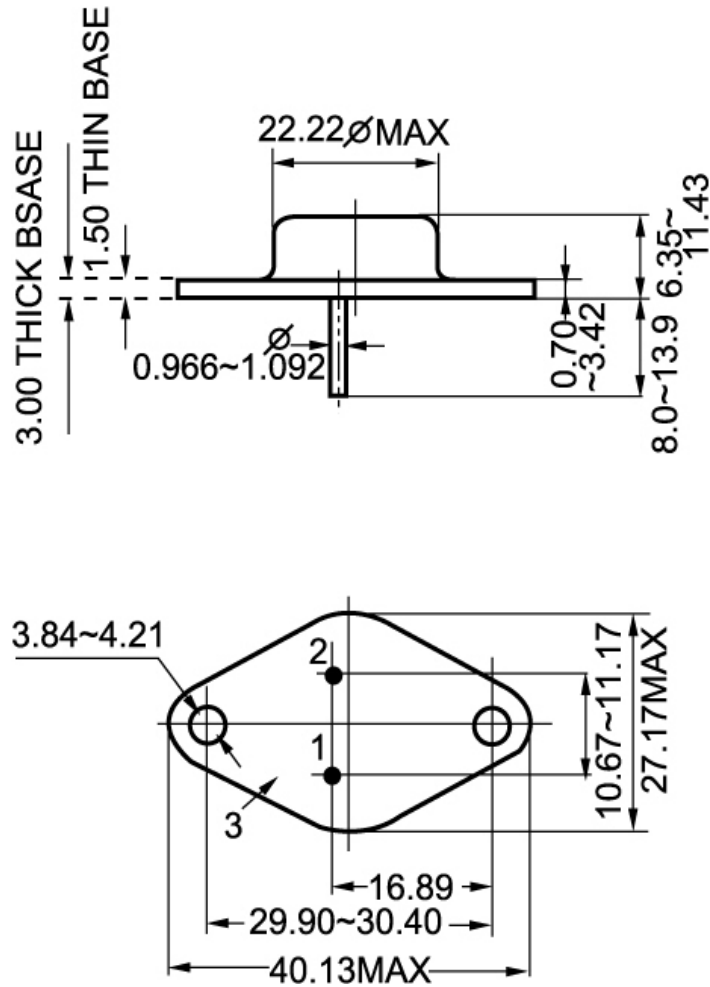


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)